

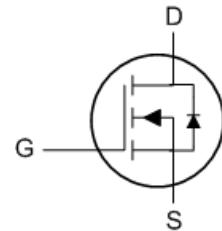
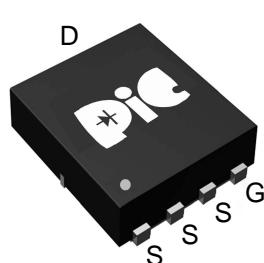
➤ General Description

This PAN20SY15SY N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ DFN5X6A-EP1



➤ Application

- DC/DC Primary Side Switch
- Industrial Synchronous
- Rectification Load Switch
- DC/DC Converters

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹	I _D @T _C =25°C	23	A
Continuous Drain Current ¹	I _D @T _C =100°C	16	A
Continuous Drain Current ¹	I _D @T _A =25°C	4.5	A
Continuous Drain Current ¹	I _D @T _A =70°C	3.8	A
Pulsed Drain Current ²	I _{DM}	60	A
Total Power Dissipation ³	P _D @T _C =25°C	72.6	W
Total Power Dissipation ³	P _D @T _A =25°C	2.7	W
Storage Temperature Range	T _{STG}	-55 to 175	°C
Operating Junction Temperature Range	T _J	-55 to 175	°C
Thermal Resistance Junction-ambient ¹	R _{θJA}	55	°C/W
Thermal Resistance Junction-Case ¹	R _{θJC}	2.0	°C/W

➤ **Electrical Characteristics (T_J=25°C Unless otherwise noted)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =250uA	150	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V , I _D =10A	---	47	56	mΩ
Static Drain-Source On-Resistance ²		V _{GS} =4.5V , I _D =10A	---	53	68	
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =120V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =120V , V _{GS} =0V , T _J =55°C	---	---	5	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _f	V _{DS} =5V , I _D =10A	---	25	---	S
Total Gate Charge	Q _g	V _{DS} =75V , V _{GS} =10V , I _D =10A	---	19	---	nC
Gate-Source Charge	Q _{gs}		---	4.5	---	
Gate-Drain Charge	Q _{gd}		---	2.6	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =75V , V _{GS} =10V , R _G =3.3Ω I _D =10A	---	18	---	ns
Rise Time	T _r		---	5.8	---	
Turn-Off Delay Time	T _{d(off)}		---	26.5	---	
Fall Time	T _f		---	4.5	---	
Input Capacitance	C _{iss}	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	1090	---	pF
Output Capacitance	C _{oss}		---	93	---	
Reverse Transfer Capacitance	C _{rss}		---	6	---	

➤ **Diode Characteristics**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,4}	I _S	V _G =V _D =0V , Force Current	---	---	20	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =10A , dI/dt=100A/μs , T _J =25°C	---	45	---	nS
Reverse Recovery Charge	Q _{rr}		---	138	---	nC

Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.Ensure that the channel temperature does not exceed 150°C.
- 4.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics

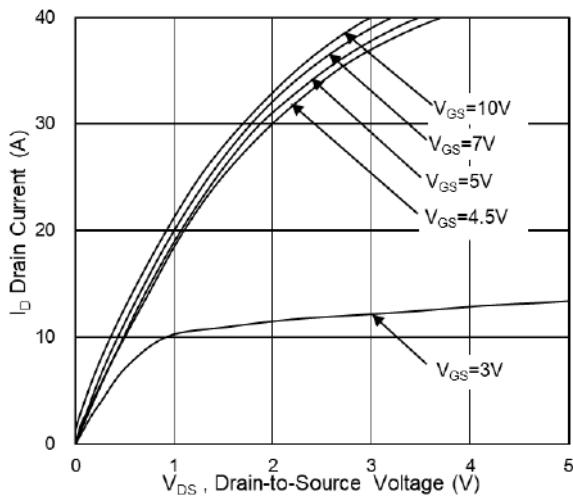


Fig.1 Typical Output Characteristics

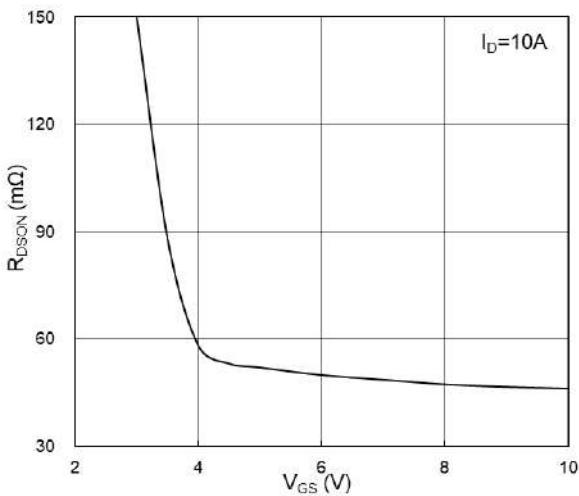


Fig.2 On-Resistance vs G-S Voltage

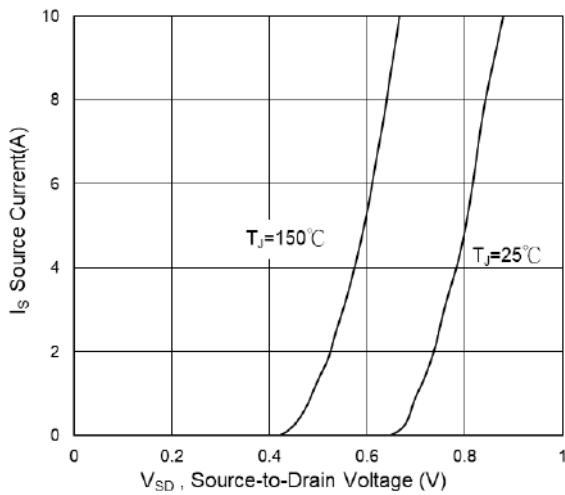


Fig.3 Source Drain Forward Characteristics

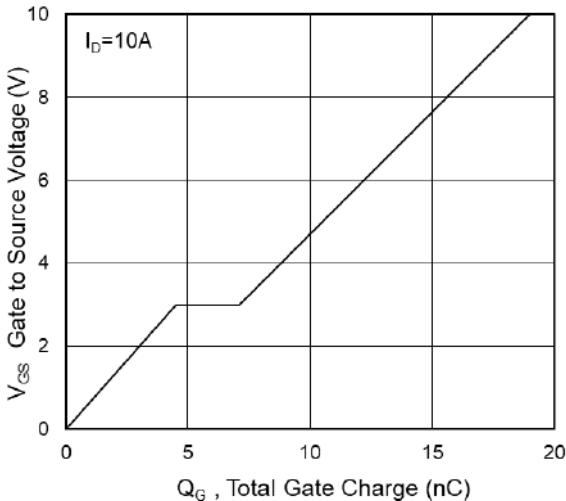


Fig.4 Gate-Charge Characteristics

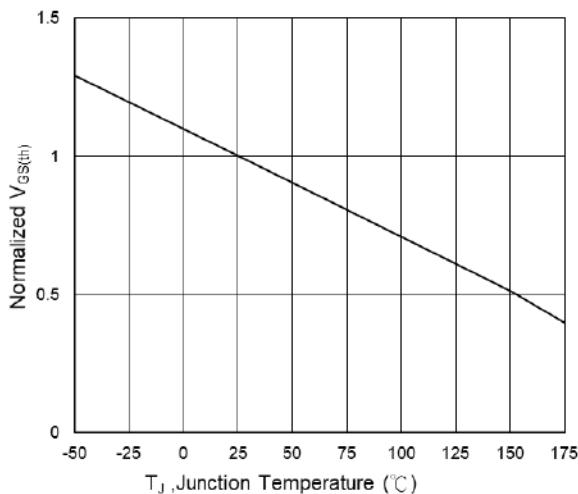


Fig.5 Normalized $V_{GS(th)}$ vs T_J

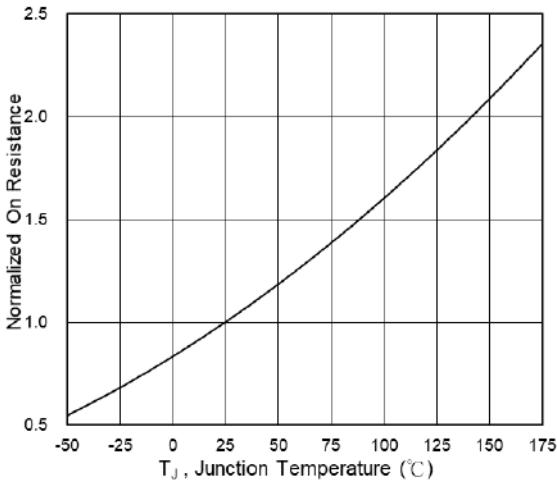


Fig.6 Normalized $R_{DS(on)}$ vs T_J

N-Ch 150V Fast Switching MOSFET
V_{DS}=150V, I_D=23A, R_{DS(ON)}=56mΩ

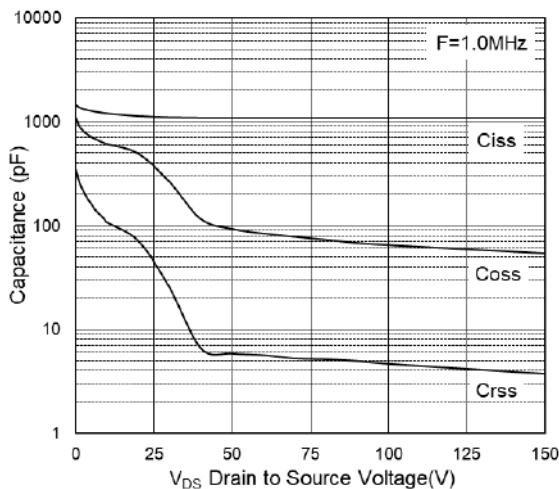


Fig.7 Capacitance

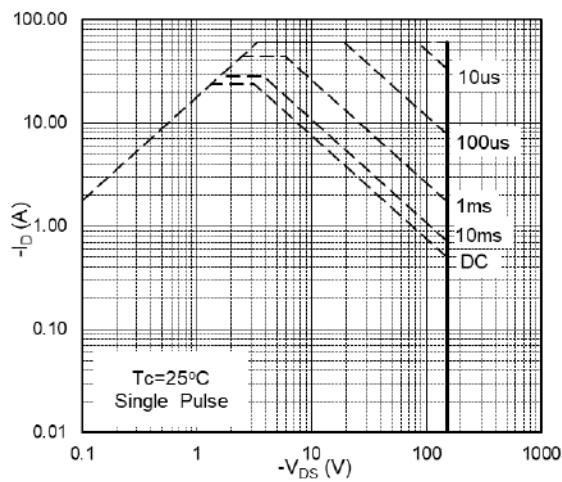


Fig.8 Safe Operating Area

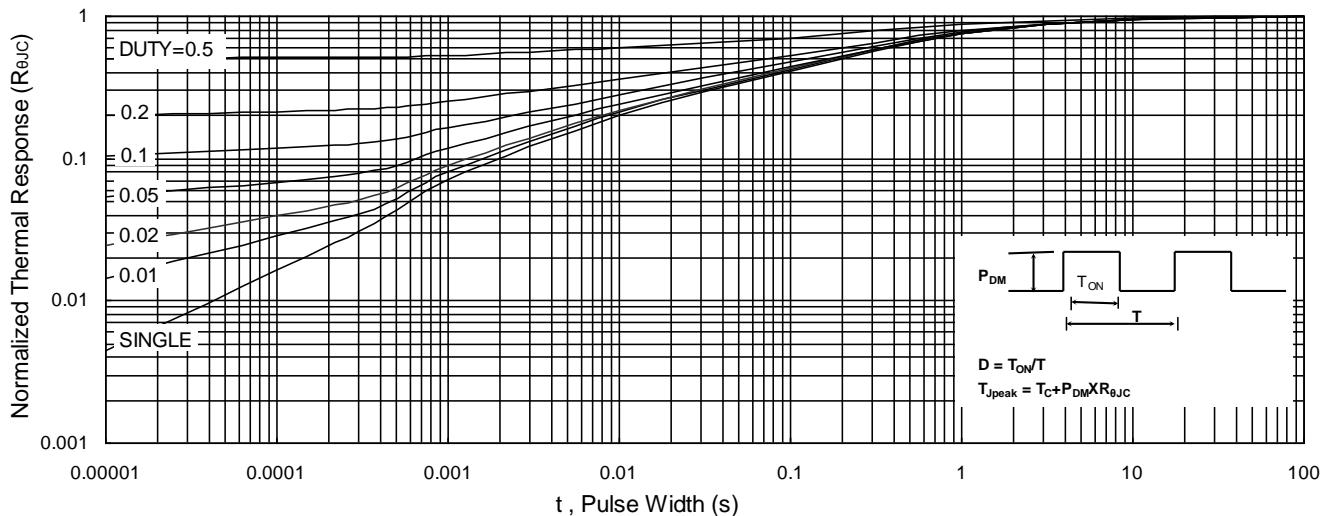


Fig.9 Normalized Maximum Transient Thermal Impedance

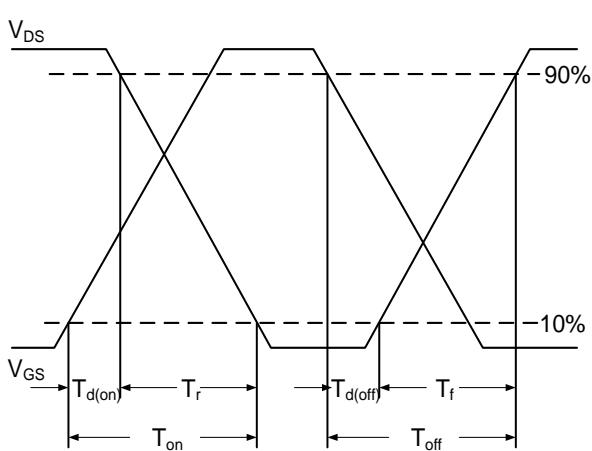


Fig.10 Switching Time Waveform

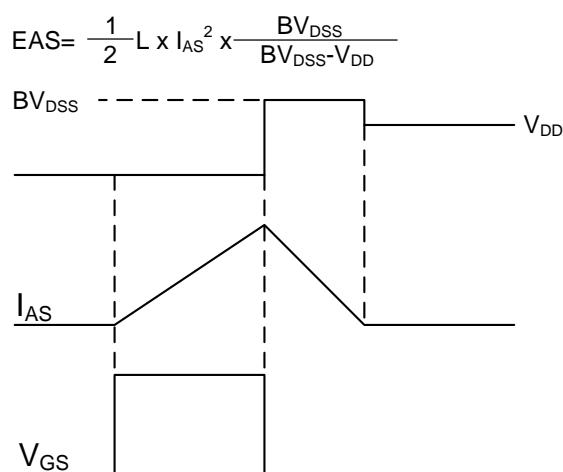
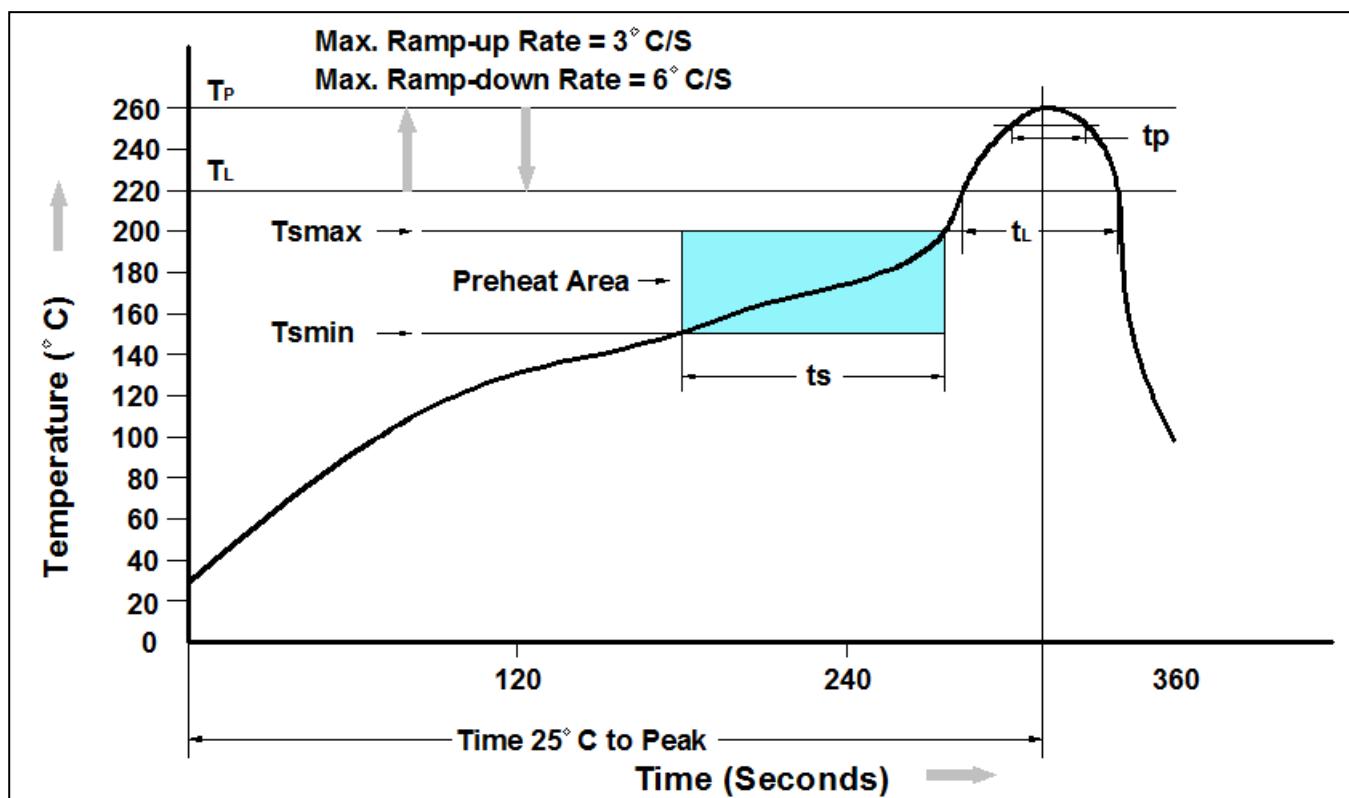


Fig.11 Unclamped Inductive Switching Waveform

➤ Recommand IR Reflow Soldering Thermal Profile

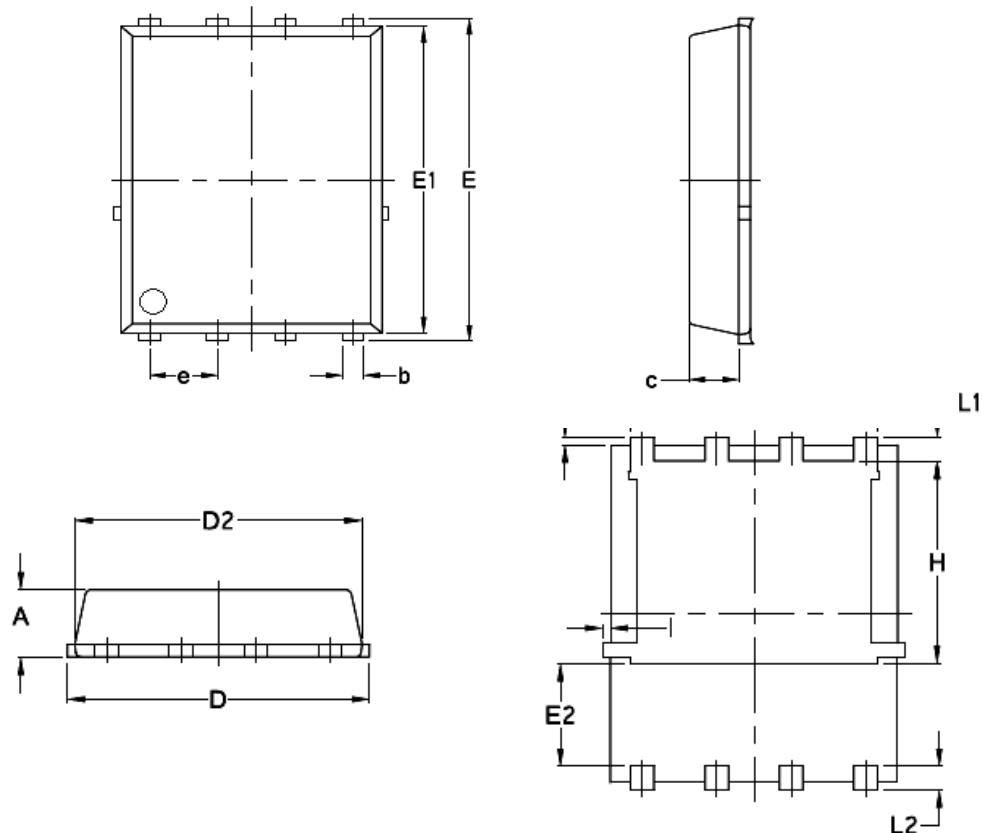


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN20SY15SY	DFN5X6A-EP1 Reel	3000 pcs

➤ **Package Information (DFN5X6A-EP1)**



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
I	---	0.18	---	0.0070
E	5.90	6.15	0.2323	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.10	---	0.0433	---
e	1.27 BSC		0.05 BSC	
H	3.30	3.78	0.1299	0.1488
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.61	0.0150	0.0240
L2	0.38	0.71	0.0150	0.0279

DISCLAIMER

- The information in this document and any product described herein are subject to change without notice and should not be construed as a commitment by Paceleader, Paceleader reserve the right to make changes to the information in this document.
- Though Paceleader make effort to improve product quality and reliability, Product can malfunction and fail due to their inherent electrical sensitivity and vulnerability to physical stress, it is the responsibility of the customer, when utilizing Paceleader products, to comply with the standards of safety in making a safe design for entire system and to avoid situation in which a malfunction or failure., In developing a new designs, customer should ensure that the device which shown in this documents are used within specified operating ranges.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by Paceleader for any infringements of patents or other rights of the third parties which may result from its use.